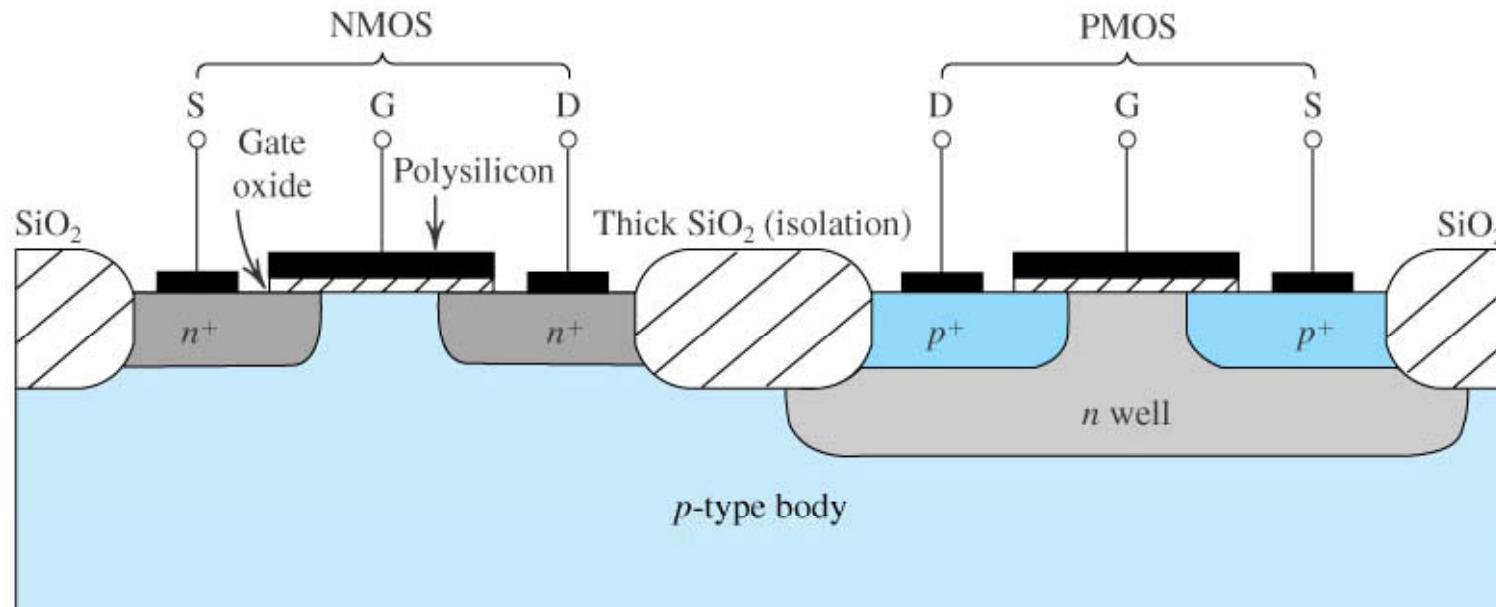
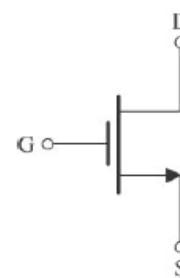


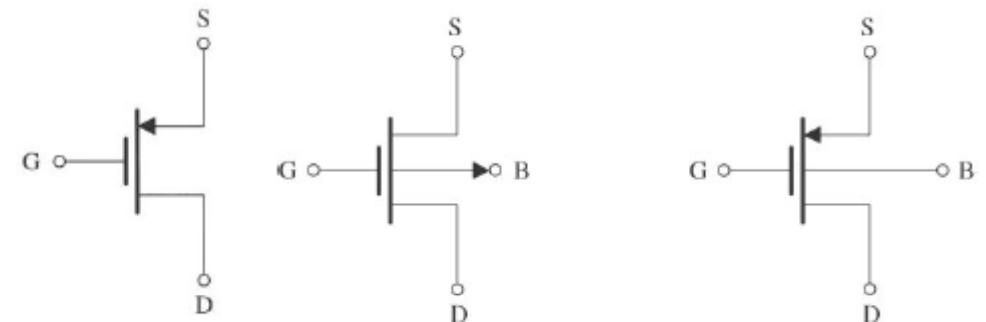
Lect. 20: PMOS



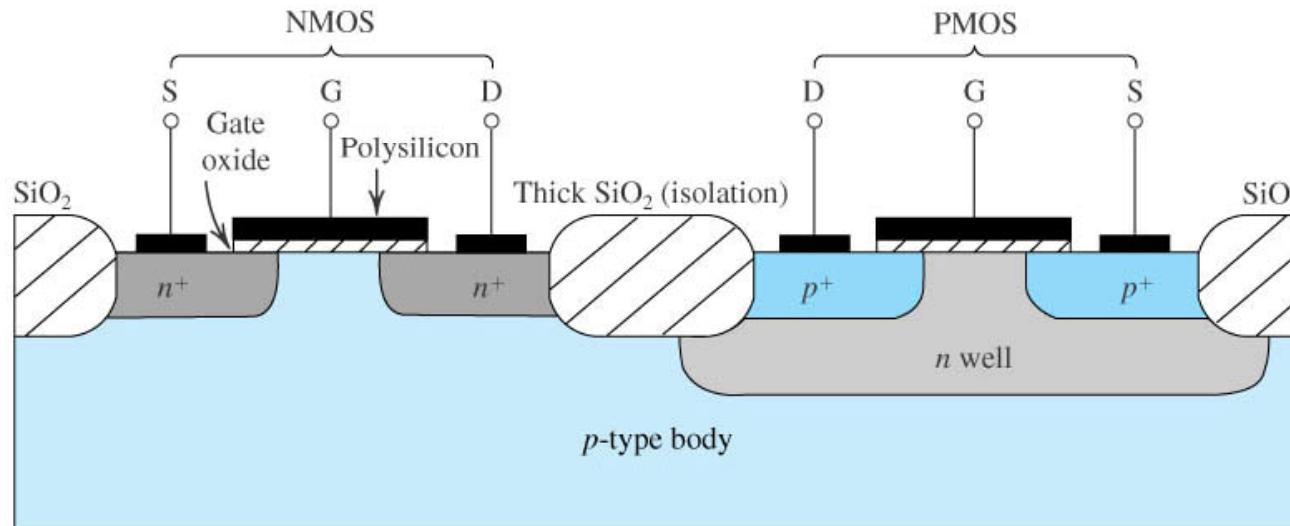
NMOS: electrons flow
from Source to Drain



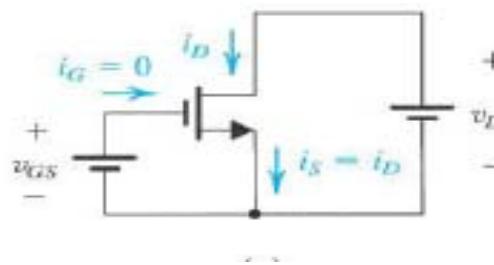
PMOS: holes flow
from Source to Drain



Lect. 20: PMOS

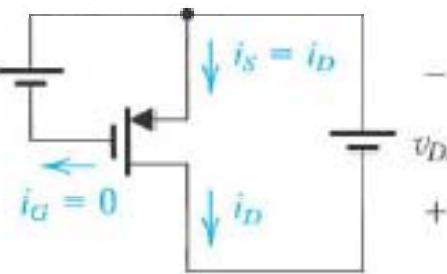


NMOS



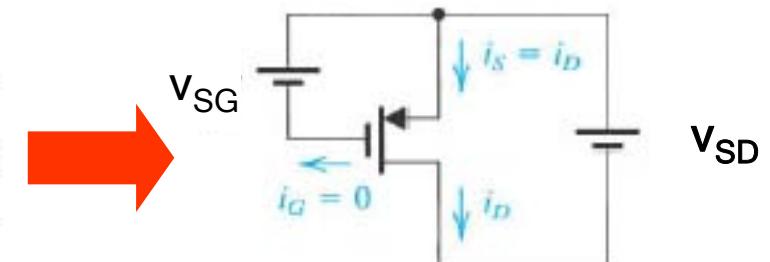
$v_{GS} > 0$ and $v_{DS} > 0$

PMOS



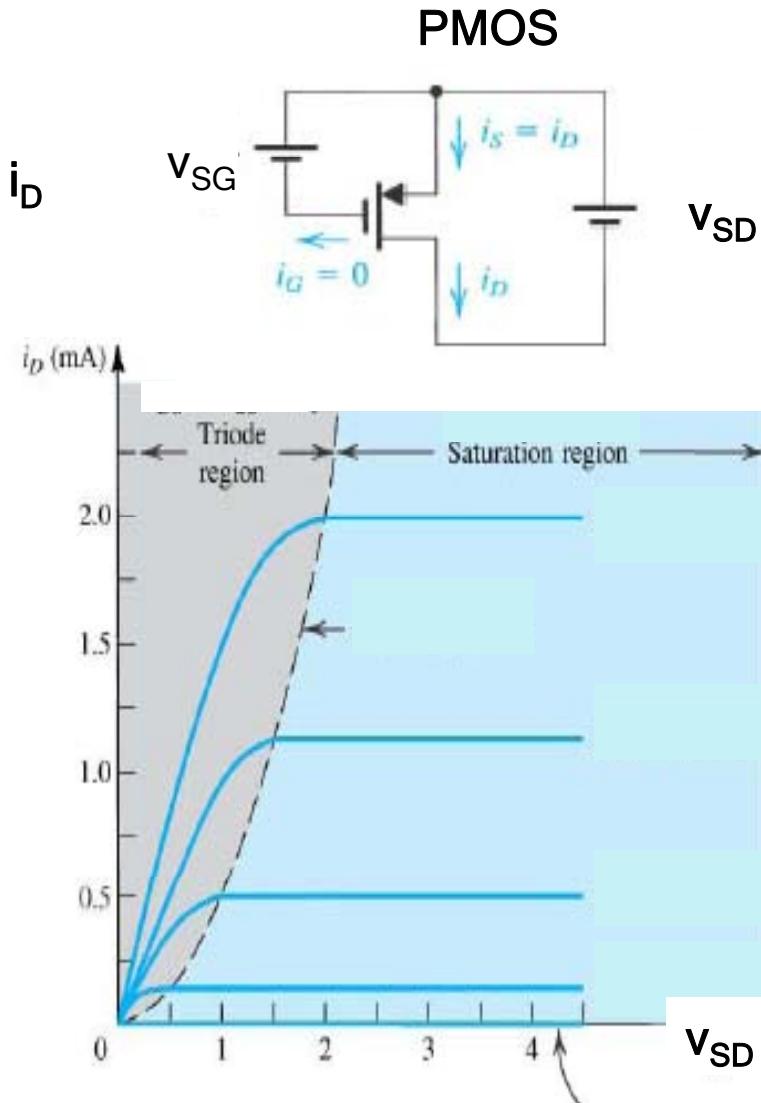
$v_{GS} < 0$ and $v_{DS} < 0$

PMOS



$v_{SG} > 0$ and $v_{SD} > 0$

Lect. 20: PMOS



$$v_{SG} < |V_t| : i_D = 0$$

$v_{SG} > |V_t|$ and $v_{SD} < v_{SG} - |V_t|$ (triode):

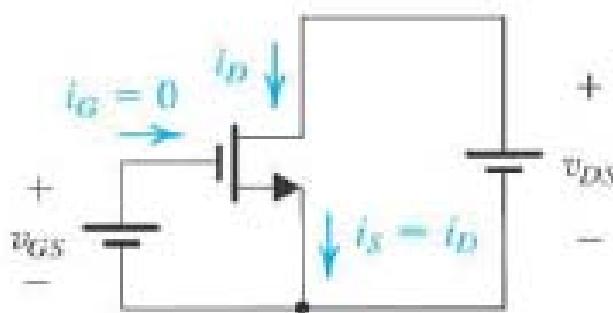
$$i_D = \mu_p C_{ox} \frac{W}{L} \left[(v_{SG} - |V_t|) \cdot v_{SD} - \frac{1}{2} v_{SD}^2 \right]$$

$v_{SG} > |V_t|$ and $v_{SD} > v_{SG} - |V_t|$ (saturation):

$$i_D = \frac{1}{2} \mu_p C_{ox} \frac{W}{L} (v_{SG} - |V_t|)^2$$

Lect. 20: PMOS

NMOS



$$v_{GS} < V_t : i_D = 0$$

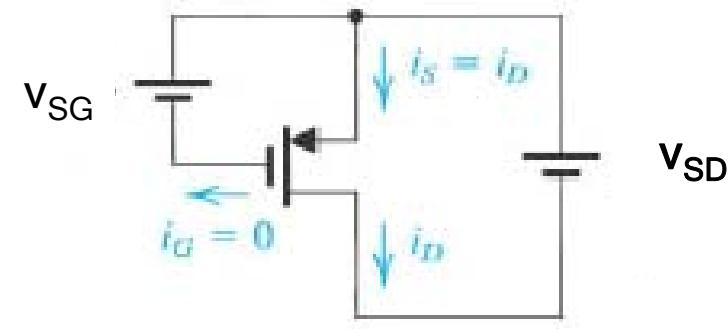
$v_{GS} > V_t$ and $v_{DS} < v_{GS} - V_t$ (triode) :

$$i_D = \mu_n C_{ox} \frac{W}{L} \left[(v_{GS} - V_t) \cdot v_{DS} - \frac{1}{2} v_{DS}^2 \right]$$

$v_{GS} > V_t$ and $v_{DS} > v_{GS} - V_t$ (saturation):

$$i_D = \frac{1}{2} \mu_n C_{ox} \frac{W}{L} (v_{GS} - V_t)^2$$

PMOS



$$v_{SG} < |V_t| : i_D = 0$$

$v_{SG} > |V_t|$ and $v_{SD} < v_{SG} - |V_t|$ (triode) :

$$i_D = \mu_p C_{ox} \frac{W}{L} \left[(v_{SG} - |V_t|) \cdot v_{SD} - \frac{1}{2} v_{SD}^2 \right]$$

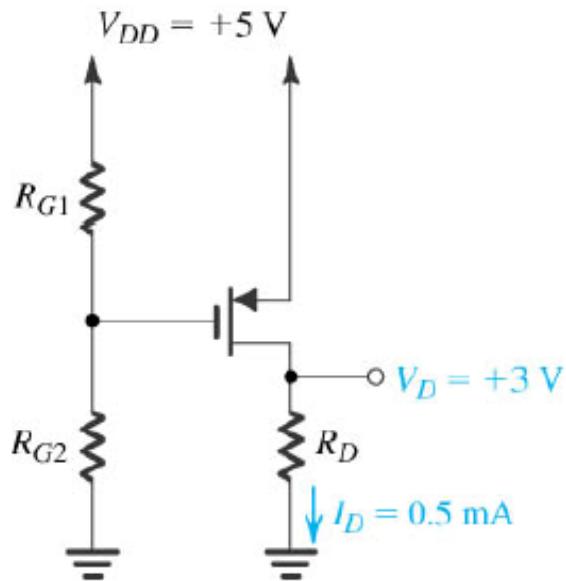
$v_{SG} > |V_t|$ and $v_{SD} > v_{SG} - |V_t|$ (saturation):

$$i_D = \frac{1}{2} \mu_p C_{ox} \frac{W}{L} (v_{SG} - |V_t|)^2$$

Lect. 20: PMOS

Example 4.6

Design the circuit so that PMOS is in saturation and $I_D = 0.5\text{mA}$, $v_D = 3\text{V}$. What is the max. R_D possible?

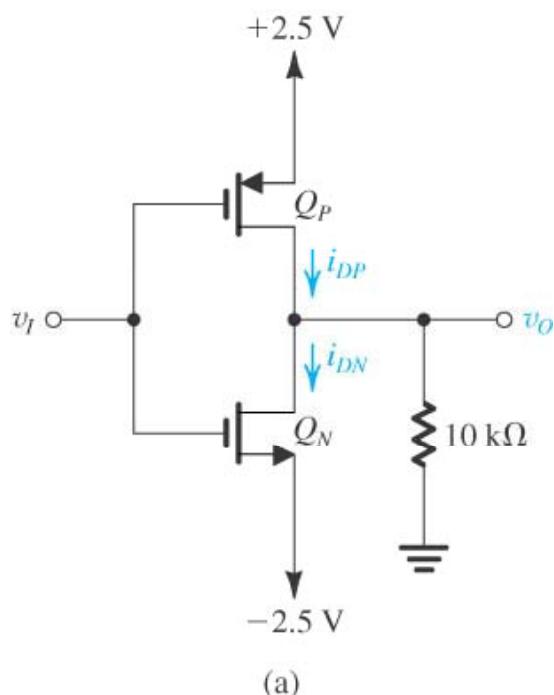


1. What is v_G ?
2. What is R_{G2}/R_{G1} ?
3. What is R_D ?
4. What happens when R_D increases?

Lect. 20: PMOS

Determine i_{Dn} , i_{Dp} , v_O for $v_I = 0, 2.5, -2.5V$.

$v_{Tn} = 1V$, $v_{Tp} = -1V$, both transistors have $k'(W/L) = 1mA/V^2$.



With $v_I = 0V$,

- Top and bottom symmetric
- $v_O = 0V$
- Both transistors in saturation
- $i_{Dn}, i_{Dp} = 1.125mA$

With $v_I = 2.5V$,

- Q_P is off and Q_N is in triode
- $i_{Dp} = 0$, $i_{Dn} = 0.244mA$

With $v_I = -2.5V$,

- Q_N is off and Q_P is in triode
- $i_{Dn} = 0$, $i_{Dp} = 0.244mA$

Lect. 20: PMOS

Homeworks:

For the following MOS circuits, determine $V_1 \dots V_7$. Use $|V_t| = 2V$, $k' W/L = 1mA/V^2$.

